



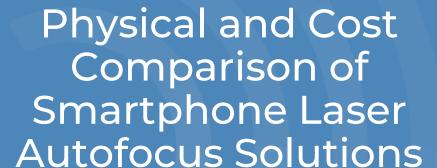








SONY



presented by P.L. Bonanno



#### YOLE GROUP

### Activities

We provide industrial companies, financial investors and R&D organizations, with market research and marketing analysis, technology, supply chain and cost analysis, as well as performance evaluation, to help our customers in their decision-making about their future business and manufacturing strategy in the semiconductor, photonic and electronic sectors.

#### **3 CORE ACTIVITIES BASED ON DEEP SYNERGIES**

#### Market & Technology

- Market, technology, and strategy consulting
- M&A, Due Diligence and evaluation of companies

# Teardown Reverse engineering and costing

- Technology, process & cost analysis
- Teardown and reverse engineering
- Comparative analysis

#### Performance analysis

- Test of electric and electro-optical performance of devices
- Comparison of performances and related technical choice



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# LASER AUTOFOCUS REVERSE COSTING

# **Presentation Outline**

- 1. Smartphone 3D Imaging and Laser Autofocus
- 2. 3 systems
  - iPhone 15 Pro LiDAR module by Sony
  - VL53L5 by STMicroelectronics
  - TMF8821 by ams AG
- 3. Reverse Costing Methodology
- 4. Approximative Model
- 5. Results & Discussion



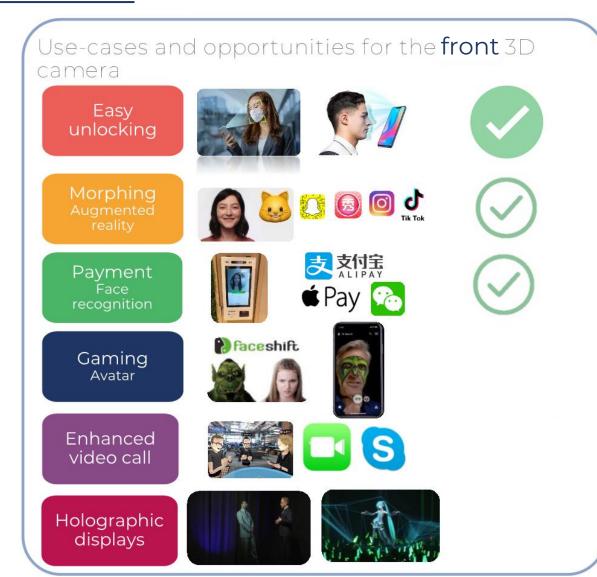
# LASER AUTOFOCUS REVERSE COSTING

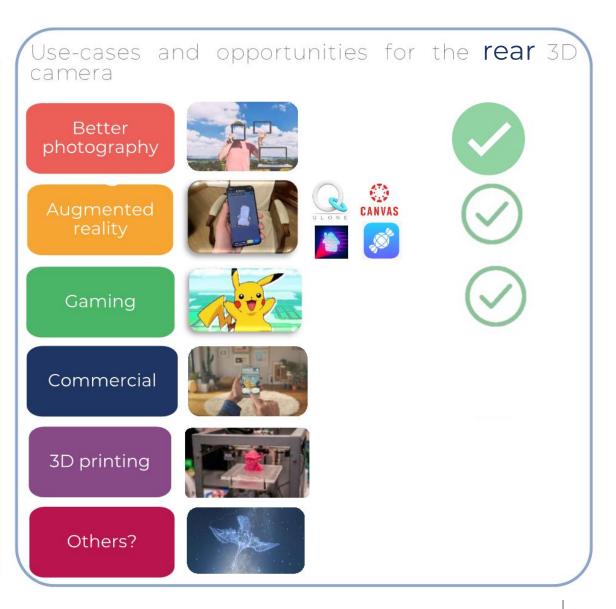
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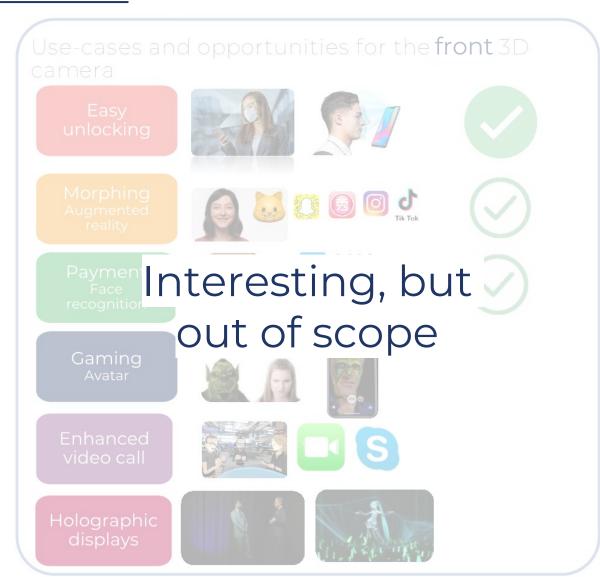
# Smartphone 3D Imaging use cases

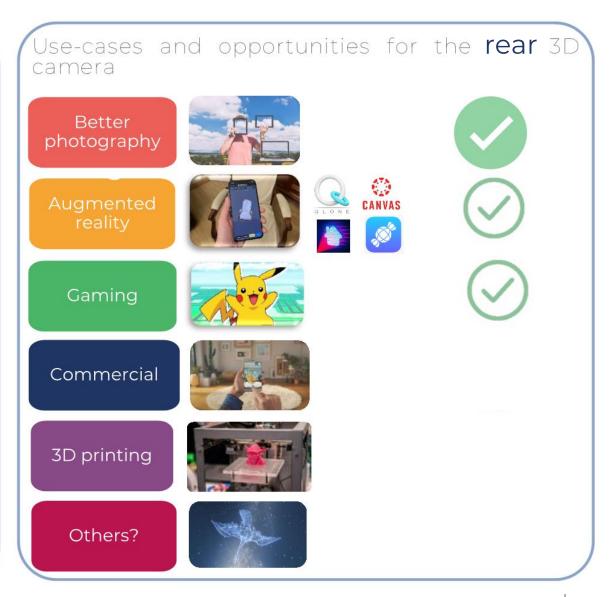






# Smartphone 3D Imaging use cases







Smartphone 3D Imaging use cases

Photography (space-resolved laser autofocus)





selective focus & bokeh



Continuous mode autofocus



Smartphone 3D Imaging use cases

# Mixed Reality Gaming







# Smartphone 3D Imaging use cases

# Commercial / Shopping



Virtual mall



Fitting clothes



AR Advertisement



Reality curation



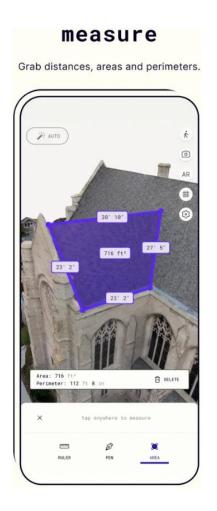
Interior decorating



# Smartphone 3D Imaging use cases

# and more...





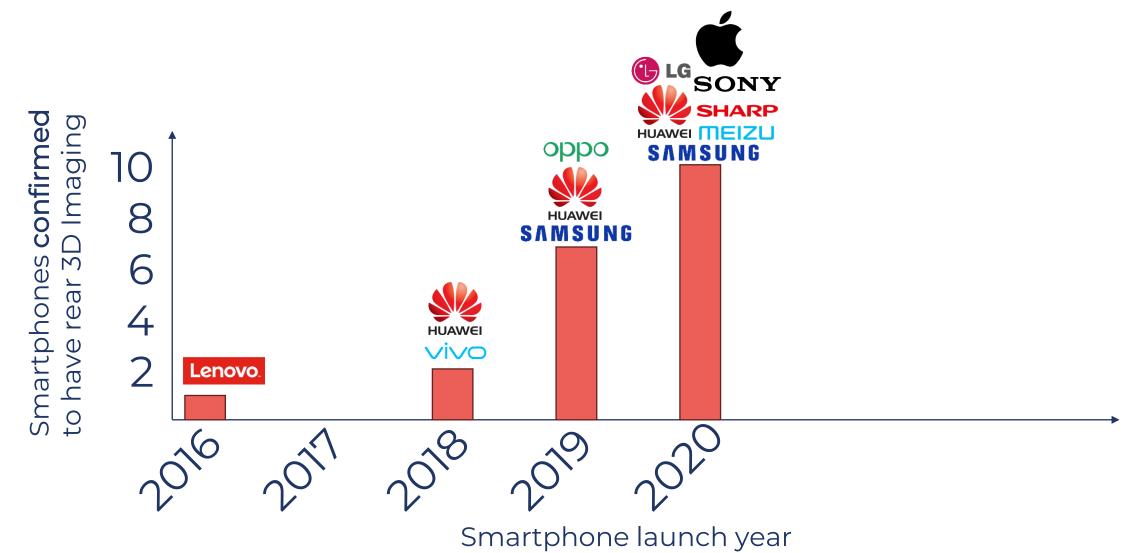






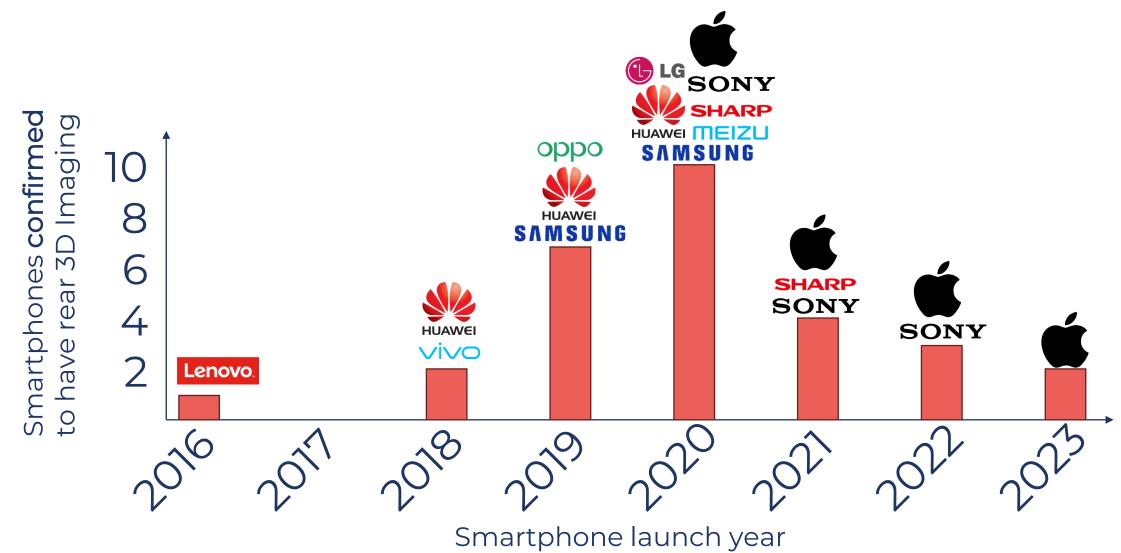


# Incidence of Rear-facing 3D Imaging



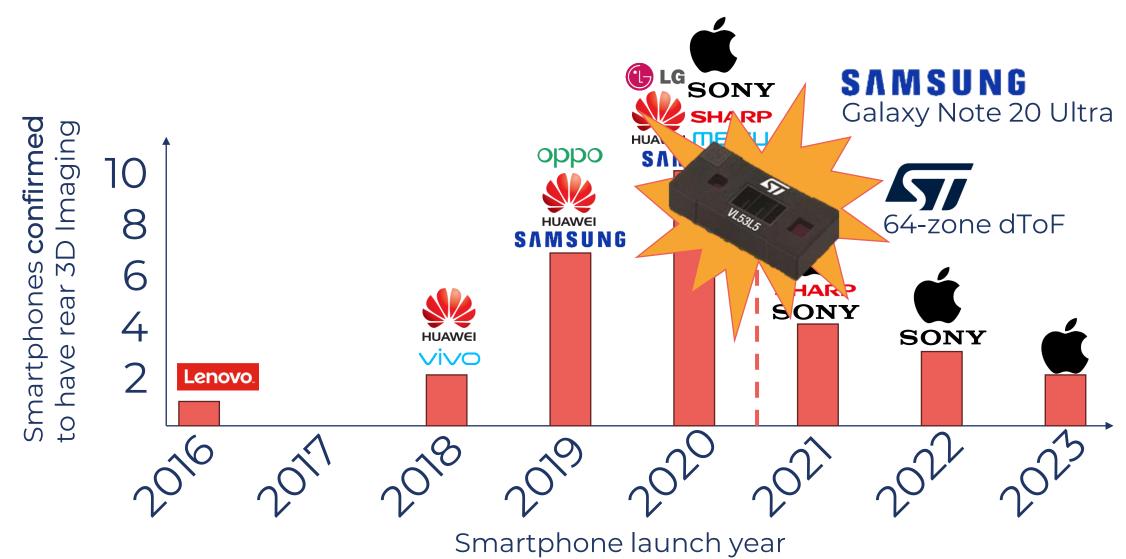


# Incidence of Rear-facing 3D Imaging



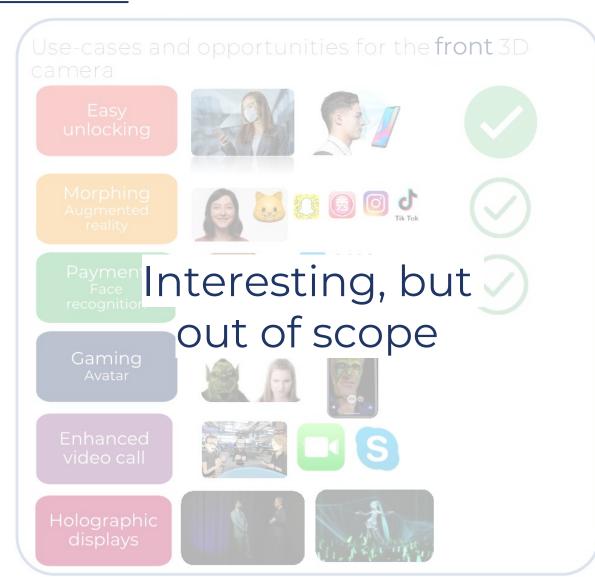


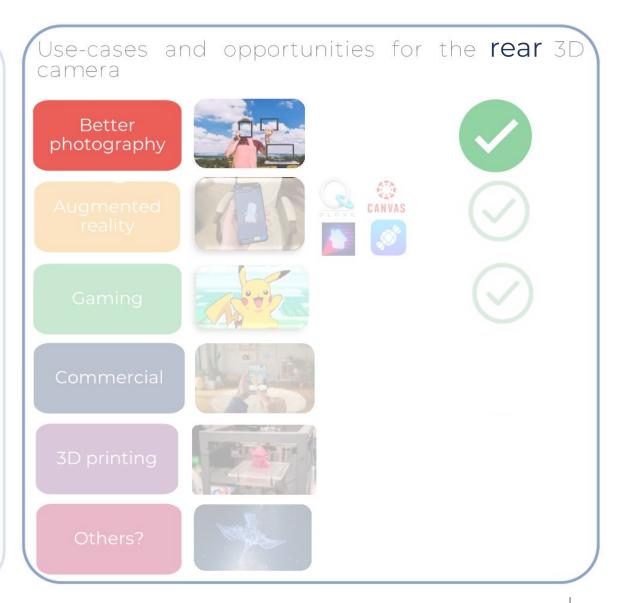
# Incidence of Rear-facing 3D Imaging





### Multizone dToF use cases



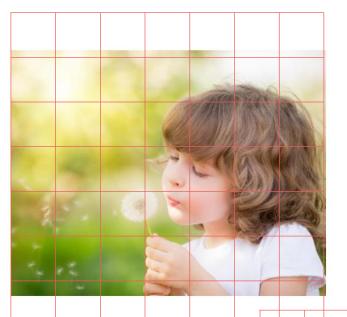


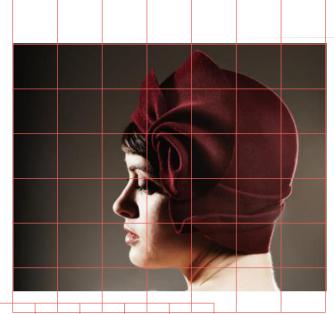


Multi-zone Laser Autofocus

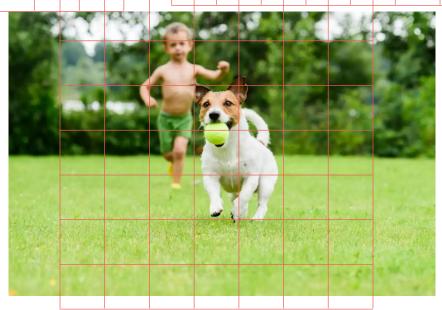
Photography (space-resolved laser autofocus)

"Multi-zone" Laser Autofocus





selective focus & bokeh



Continuous mode autofocus



Ultra-premium Smartphone Autofocusing Strategies

# Passive Autofocus



Uses special pixels in the CIS

- Very Inexpensive
- Needs bright, high contrast scene

used by all smartphones

# **Active Autofocus**



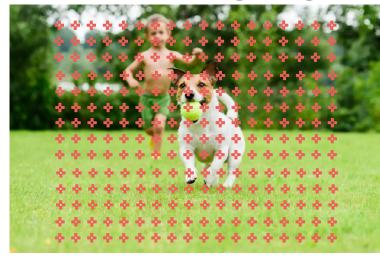


**HONOR** 

- Moderate cost
- Low resolution







- High cost
- High resolution





# LASER AUTOFOCUS REVERSE COSTING

# **Presentation Outline**

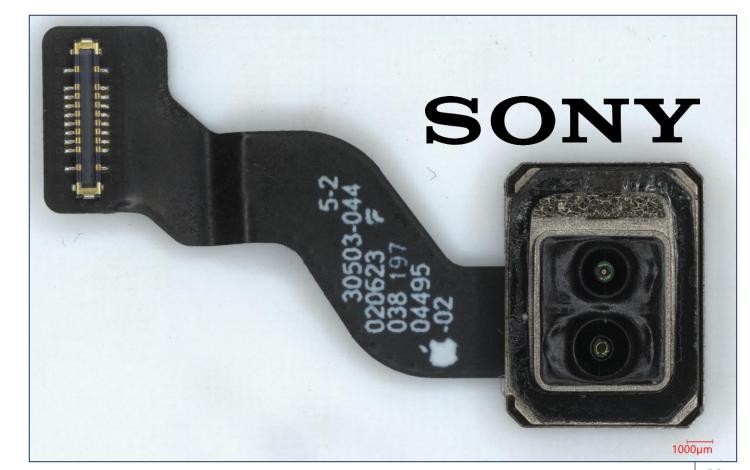




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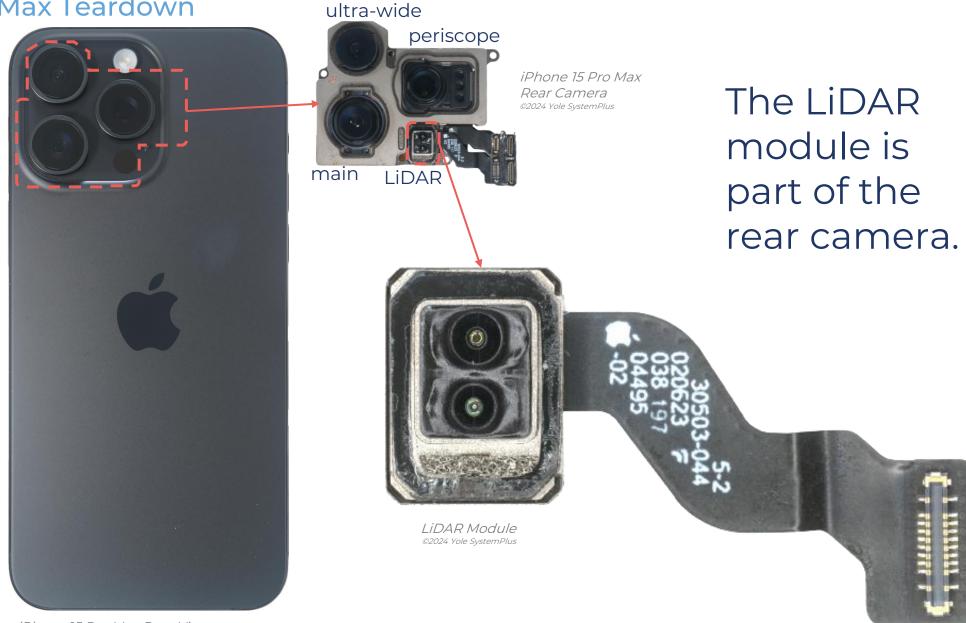




# SONY

# **IPHONE 15 PRO LIDAR MODULE**

iPhone 15 Pro Max Teardown

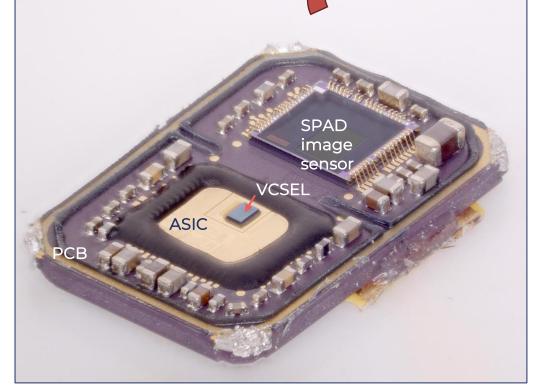


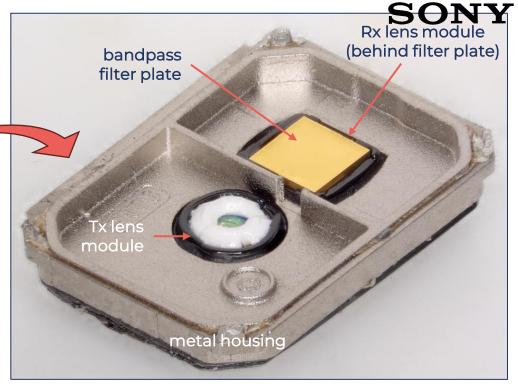


# Module Teardown



separate optics assembly from substrate





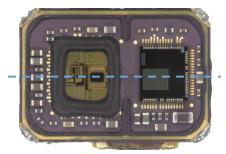
LiDAR Module Optics Assembly - Perspective View
©2024 Yole SystemPlus

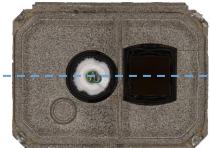


LiDAR Module /with optics removed - Perspective View
©2024 Yole SystemPlus

### **Cross Section**





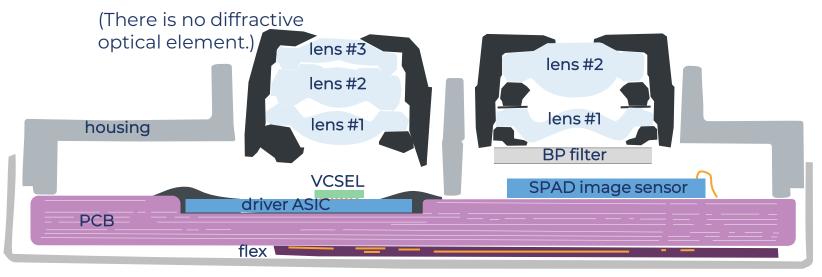


Opened LiDAR Module w/ cross-sectional plane indicated - Optical Views ©2024 Yole SystemPlus

The 3 active dies, the driver ASIC, SPAD image sensor and VCSEL, are all supplied by Sony.

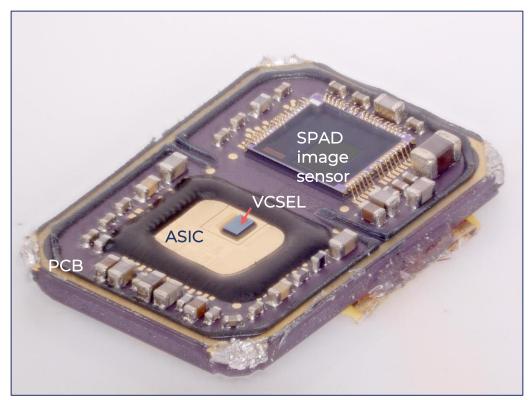


LiDAR Module Cross Section - Optical View @2024 Yole SystemPlus



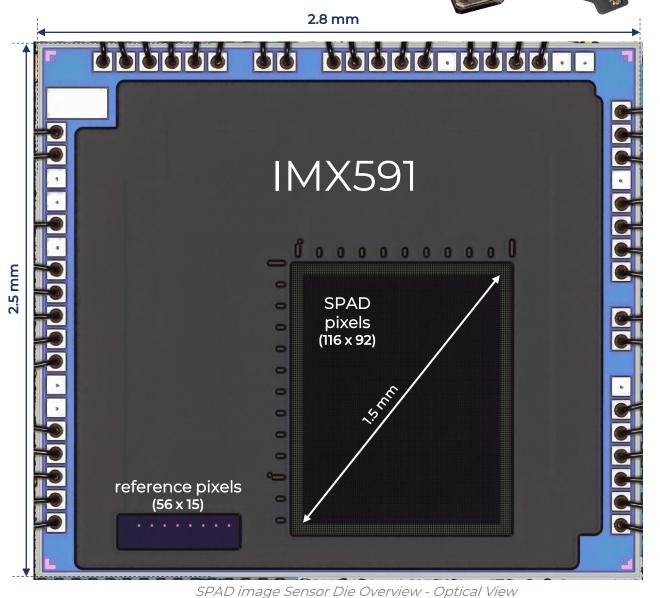


# **SPAD CIS Overview**



LiDAR Module /with optics removed - Perspective View

# 0.01 Mp SPAD CIS 10 µm SPAD pixel



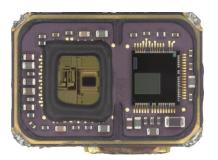
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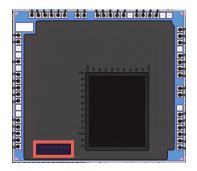
# Window



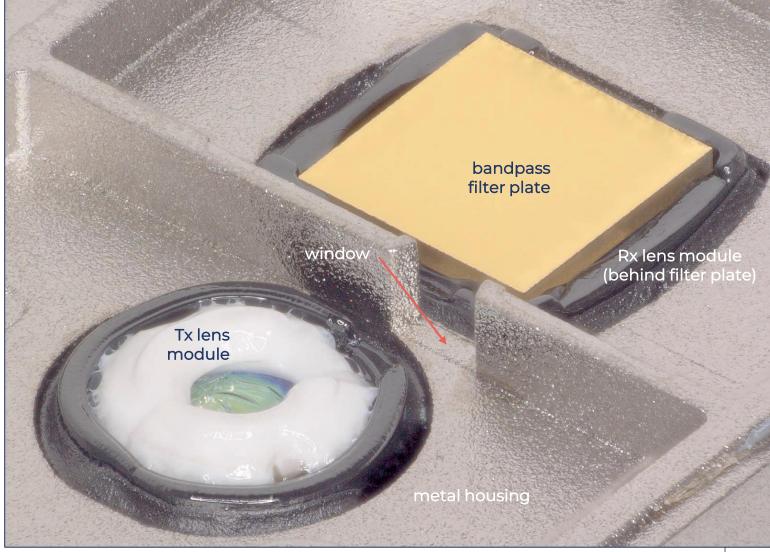




Opened LiDAR Module -Optical Views ©2024 Yole SystemPlus



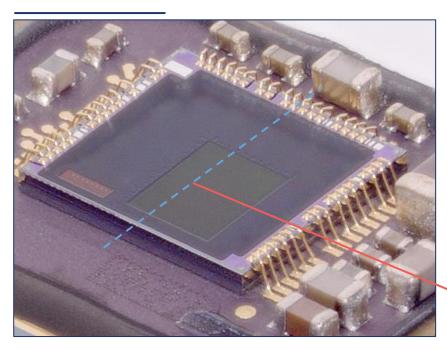
A window in the lightblocking wall transmits a small portion of the emission to give a t=0 signal for dToF. We hypothesize that all histogramming is handled by the CIS.





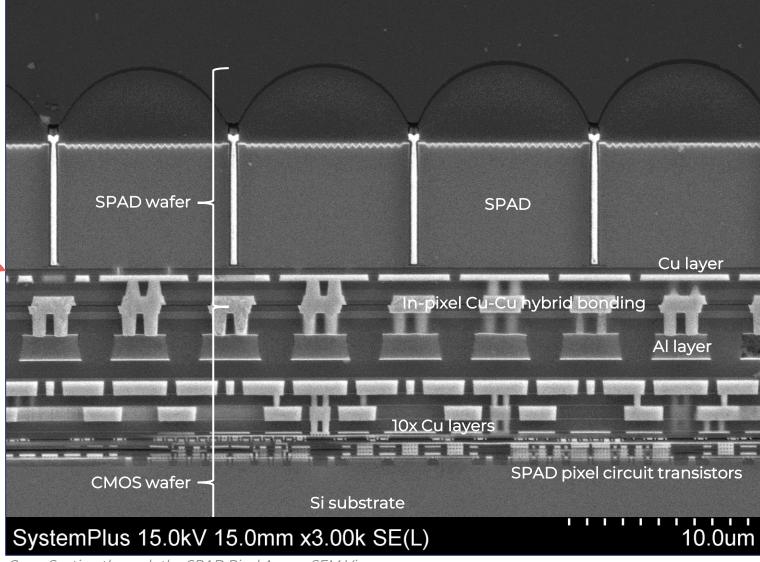
# **SPAD CIS Overview**





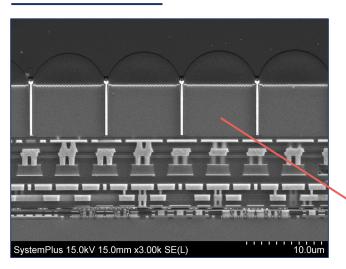
Opened LiDAR Module w/ cross-sectional plane indicated - Optical View ©2024 Yole SystemPlus

# 3D integrated BSI



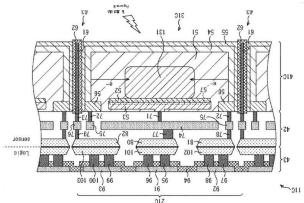


# **SPAD CIS Overview**

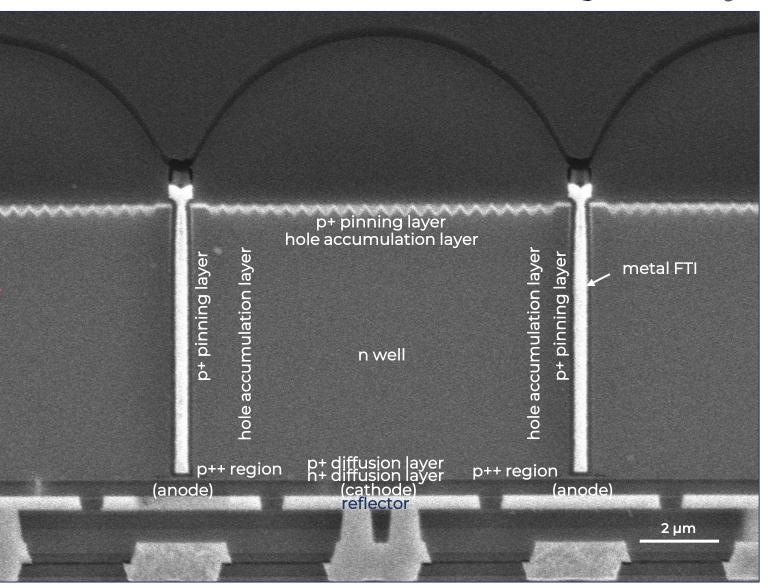


Cross Section through the SPAD Pixel Array

- SEM View ©2024 Yole SystemPlus



[1] Sony semiconductor patent Publication number JP,2018-088488A



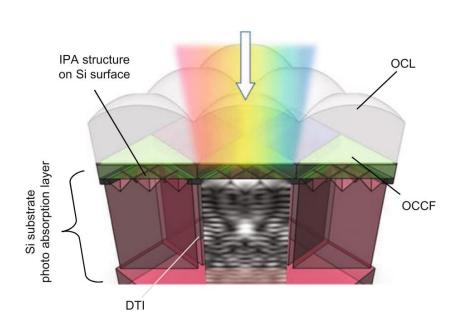
Cross Sections of BSI SPAD with 3D Integration - SEM View @2024 Yole SystemPlus



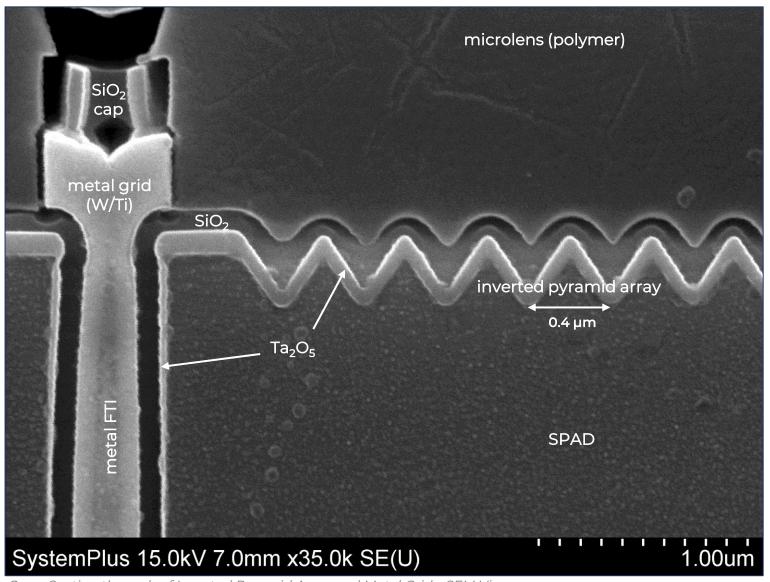
SONY

# **SPAD CIS Overview**





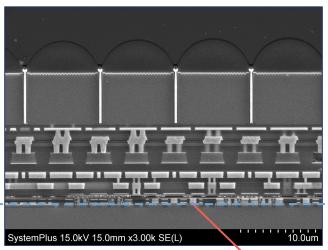
Yokogawa, S., Oshiyama, I., Ikeda, H. *et al.* IR sensitivity enhancement of CMOS Image Sensor with diffractive light trapping pixels. *Sci Rep* **7**, 3832 (2017). https://doi.org/10.1038/s41598-017-04200-y



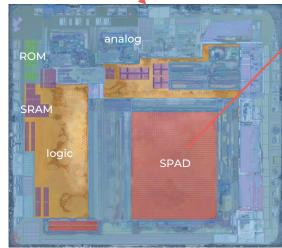
Cross Section through of Inverted Pyramid Array and Metal Grid - SEM View ©2024 Yole SystemPlus



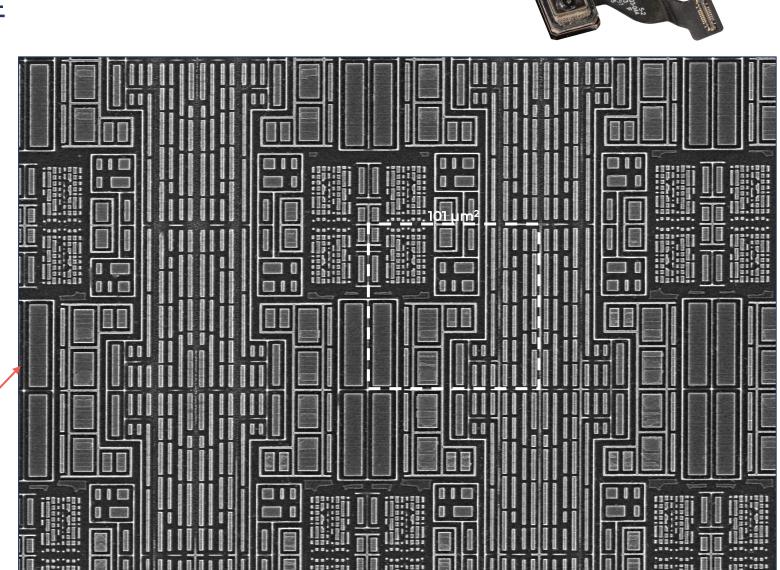




Cross Section through the SPAD Pixel Array - SEM View ©2024 Yole SystemPlus



Die Overview w/ Main Blocks
©2024 Yole SystemPlus







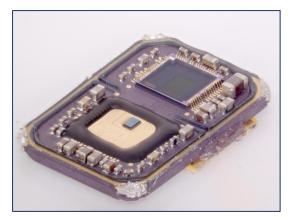
10 µm

SONY

# **IPHONE 15 PRO LIDAR**

# **VCSEL+Driver Overview**

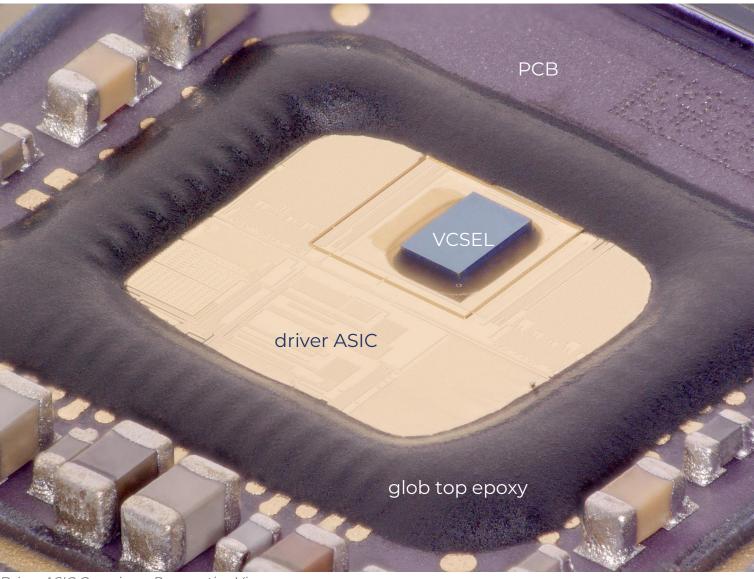




LiDAR Module /with optics removed - Perspective View @2024 Yole SystemPlus

The VCSEL is flip-chip bumped directly onto the driver ASIC.

Wirebonds are covered by glob top epoxy.

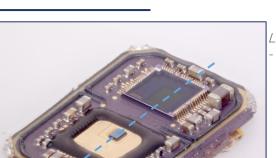


Driver ASIC Overview - Perspective View ©2024 Yole SystemPlus

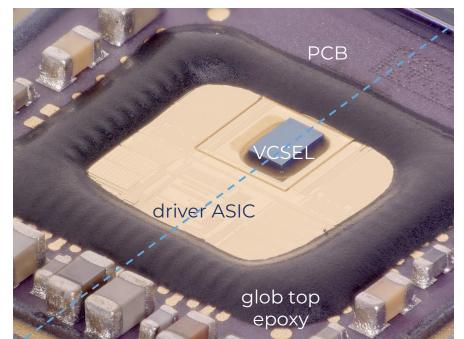


# REVERSE COSTING METHODOLOGY

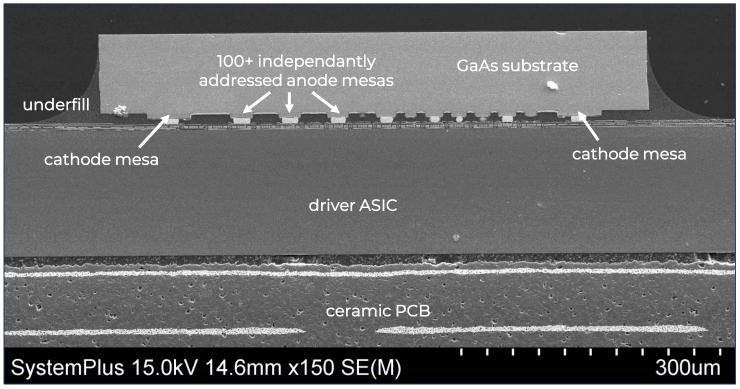
# **VCSEL+Driver Overview**



LiDAR Module /with optics removed - Perspective View ©2024 Yole SystemPlus



Driver ASIC Overview - Perspective View
©2024 Yole SystemPlus



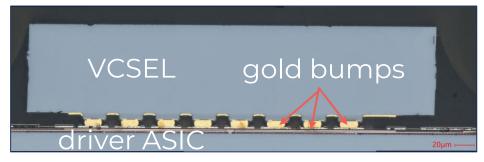




SONY

#### REVERSE COSTING METHODOLOGY

# **VCSEL+Driver Overview**



Cross-Section of VCSEL showing gold-bump connections to the driver ASIC - Optical View ©2024 Yole SystemPlus



Bottom View of VCSEL with underfill partially removed - Optical View ©2024 Yole SystemPlus

The VCSEL is gold bumped to the driver ASIC such that every anode is independently addressed. The cathode is shared. There are a total of 122 bumps.

This is a cost-saving strategy as it removes the need for the diffractive optic.





Top View of Driver ASIC where it connects to the VCSEL - Optical View ©2024 Yole SystemPlus

# LASER AUTOFOCUS REVERSE COSTING

# **Presentation Outline**

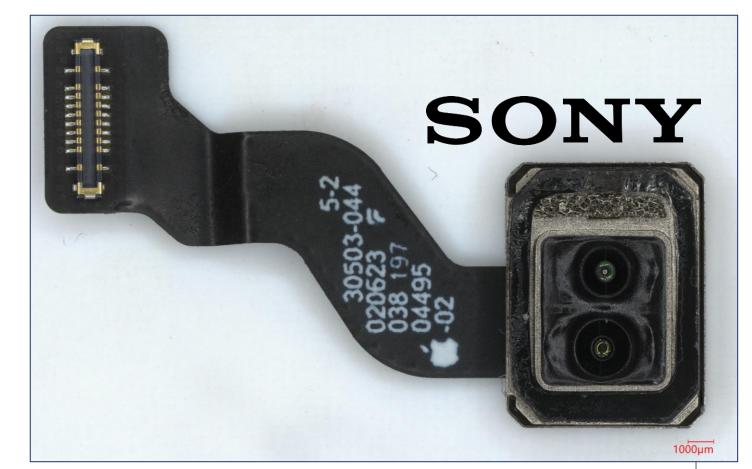




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# VL53L5

# Galaxy S22 Ultra Teardown

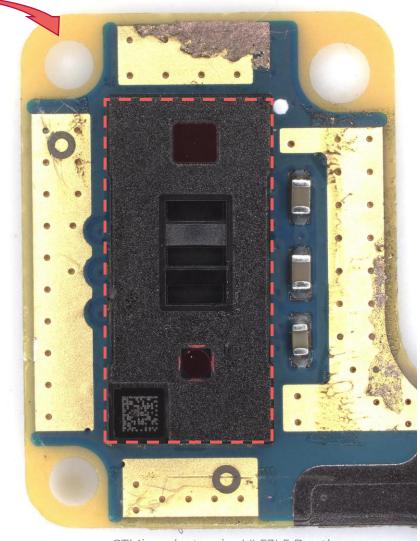
We've also found the VL53L5 in the

- Galaxy S21 Ultra,
- Galaxy Note20 Ultra,
- Xiaomi 12S Ultra,
- Xiaomi Mi 11 Ultra, and Meizu 20 INF





Samsung Galaxy S22 Ultra - Back and Opened Views
©2024 Yole SystemPlus



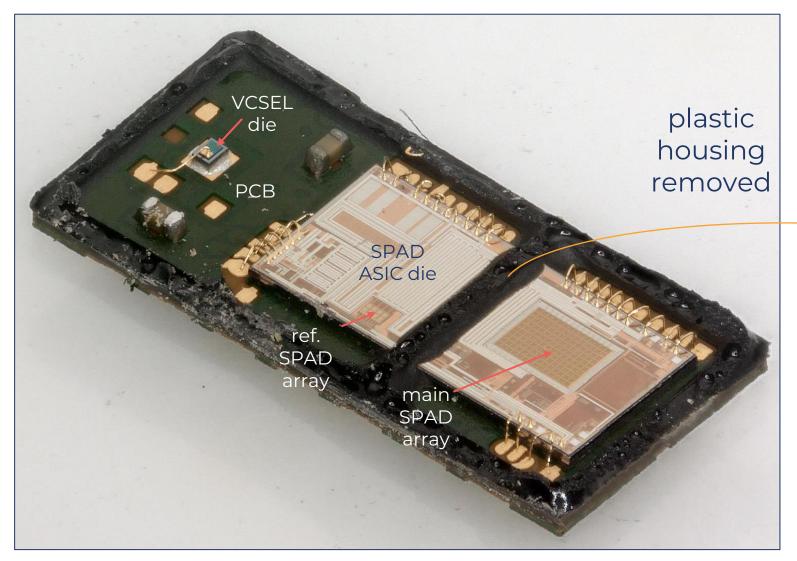
STMicroelectronics VL53L5 Depth Ranger Module on Smartphone PCB ©2024 Yole SystemPlus



# VL53L5

# Module Teardown







Plastic Housing w/ Diffuser and Fresnel Lens - Bottom View
©2024 Yole SystemPlus

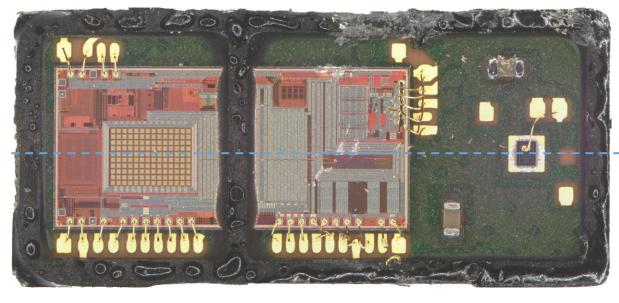
The diffuser and Fresnellike lens are glued into the plastic housing.

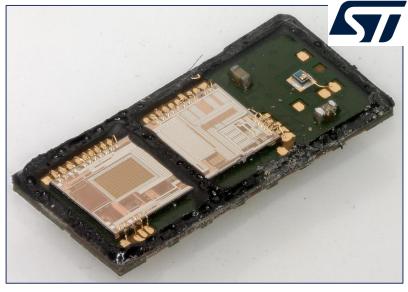


# VL53L5

# **Cross Section**



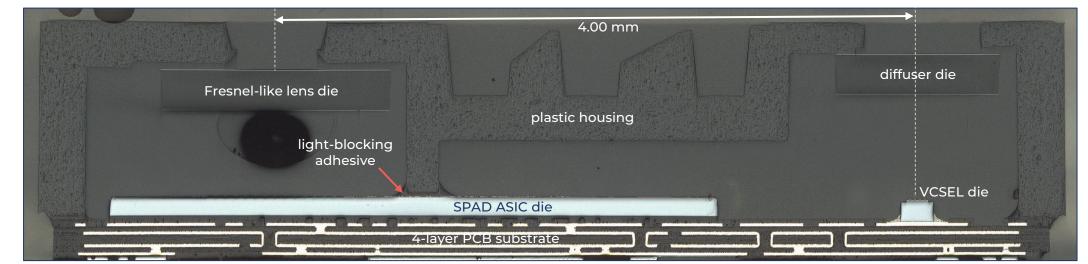




Tilted Top View of Opened Module (image mirrored left-right) ©2024 Yole SystemPlus

Top View of Opened Module showing the Cross-Sectional Plane

©2024 Yole SystemPlus







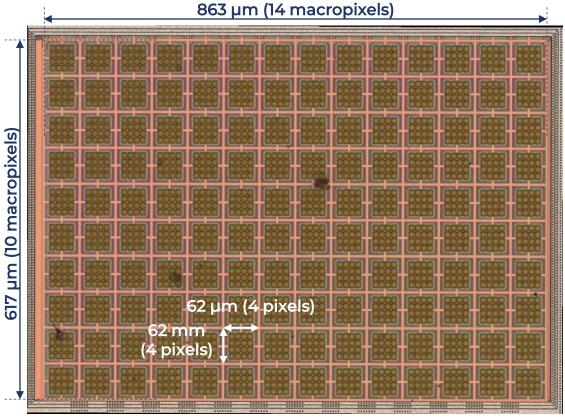


- Diffractive optics are embossed polymer on glass
- Microlenses on SPAD pixels



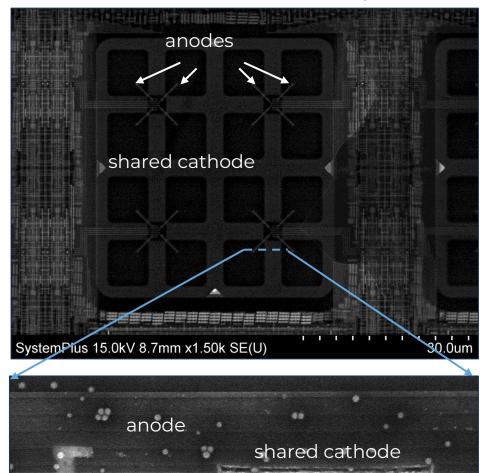


#### SPAD Overview - SEM View ©2024 Yole SystemPlus



SPAD ASIC Die Overview - Optical View ©2024 Yole SystemPlus

- 3. S. Pellegrini et al., "Industrialised SPAD in 40 nm technology," IEEE International Electron Devices Meeting (IEDM) 2017, doi: 10.1109/IEDM.2017.8268404.
- 4. S. Pellegrini. "Industrialized SPADs in deep-submicron CMOS technology." ISSW 2018.
- 5. Bruce Rae and Pascal Mellot, "A SPAD-based, Direct Time of Flight, 64 Zone, 15fps, Parallel Ranging Device Based on 40nm CMOS SPAD Technology." ISSW 2018.



SPAD Section - SEM View ©2024 Yole SystemPlus

deep n well

n well

p well

1 µm

### LASER AUTOFOCUS REVERSE COSTING

### **Presentation Outline**

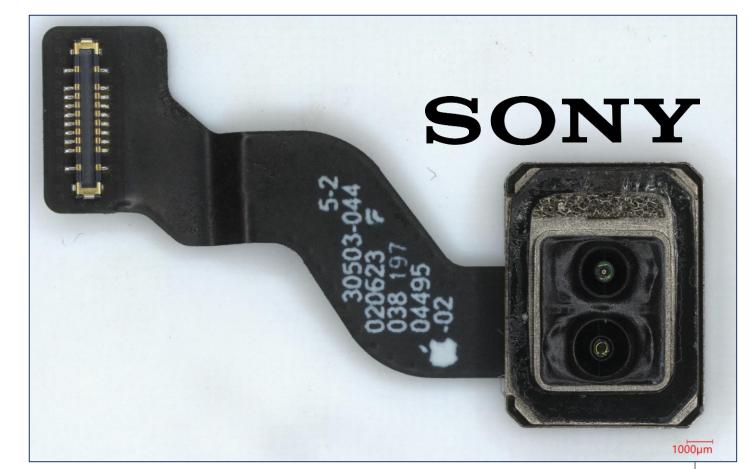




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### amin

# Magic3 Pro Teardown

We've also found the TMF8821 in the

- Honor Magic 5 Pro
- Honor Magic V2

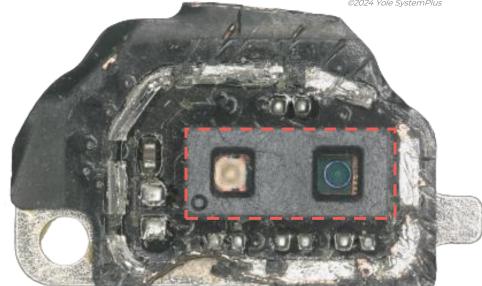








ams TMF8821 Depth Ranger Module on Smartphone PCB with Metal Cap Separated
©2024 Yole SystemPlus

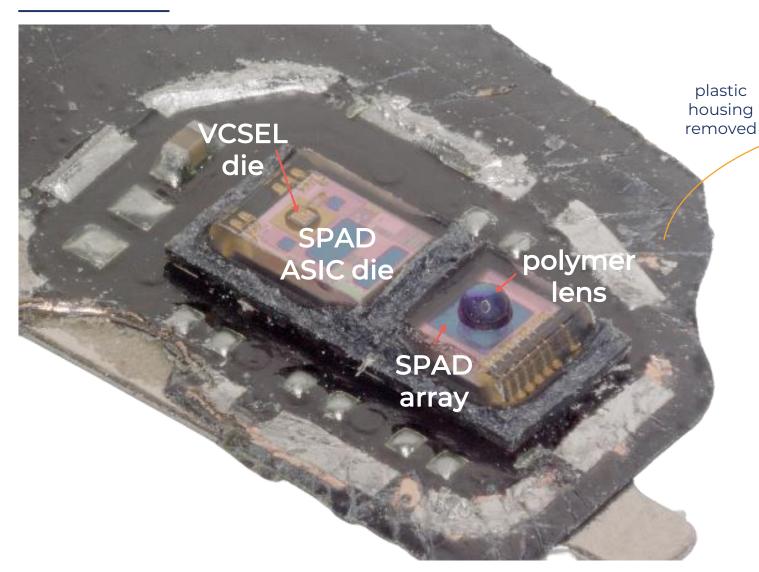


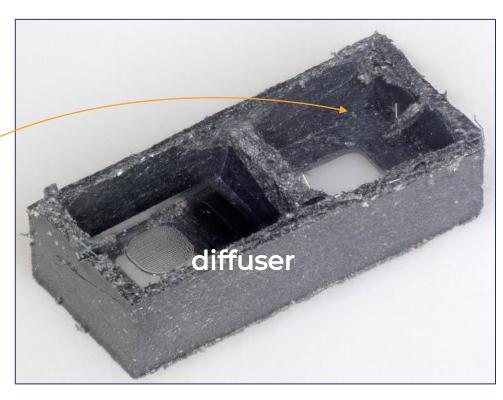


### TMF8821

### amu

### Module Teardown





Plastic Housing w/ Diffuser - Tilted View
©2024 Yole SystemPlus

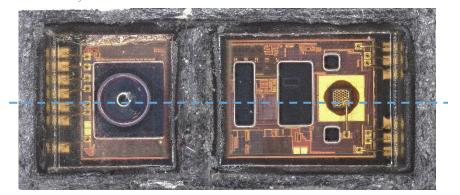


ams TMF8821 Module with Plastic Housing Removed - Tilted View

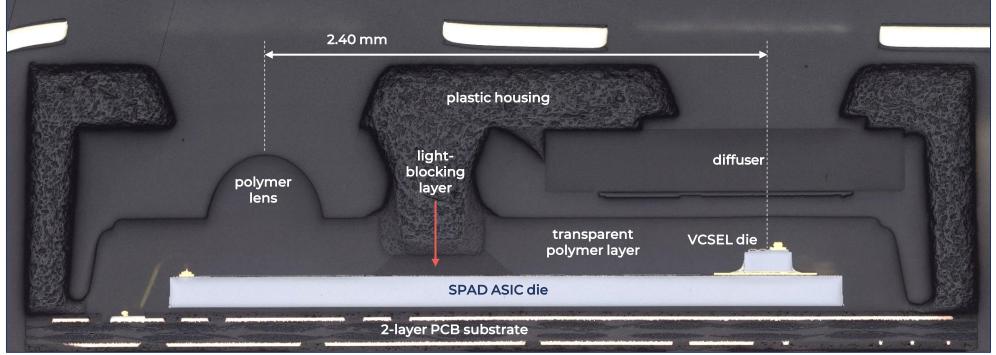
### TMF8821

## **Cross Section**

Top View of Opened Module showing the Cross-Sectional Plane
©2024 Yole SystemPlus











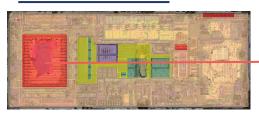
TMF8821 **Optics & VCSEL** diffusive texture 100 µm WLO Lens SPAD array  $3.5 \mu m$ SiO<sub>2</sub>/SiN optical layers VCSEL nPlus 15.0kV 7.6mm x18.0k SE(U,LA3)

- Tx optic is embossed polymer on glass
- Rx optics are onchip
- powerful VCSEL

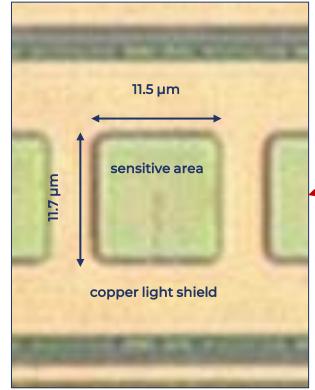


# TMF8821

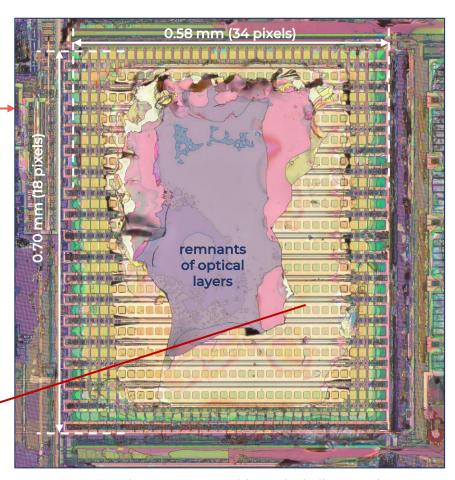
### SPAD Array



SPAD ASIC Die with Main Blocks Identified ©2024 Yole SystemPlus

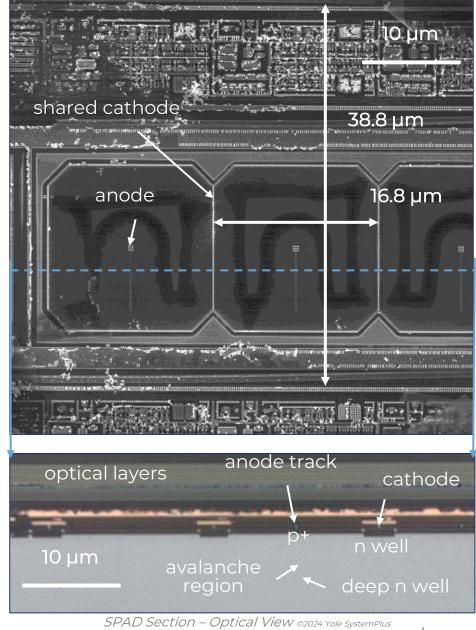


SPAD Pixel Active Area - Optical View ©2024 Yole SystemPlus



Main SPAD Array with Optical Filters and Metal Layers Partially Removed - Optical View ©2024 Yole SystemPlus

[5] R. Kappel. "Multizone, Multiobject D-TOF System in 55nm." ISSW2018.





amu

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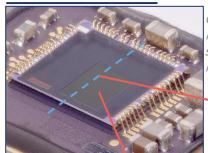
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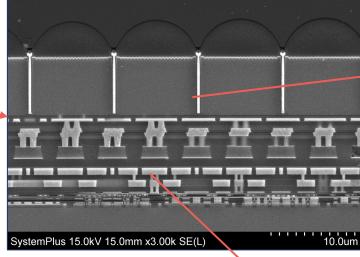
- « Reverse Costing Methodology »
  - 1. Detailed Physical Analysis
  - 2. Reverse Engineer Manufacturing Process
  - 3. Supply Chain & Financial Analysis
  - 4. Simulate Manufacturing Process to Calculate Cost



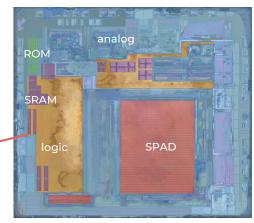
### **Detailed Physical Analysis**



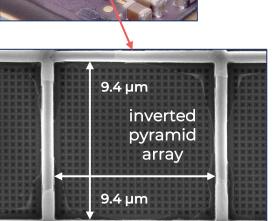
Opened LiDAR Module w/ crosssectional plane indicated - Optical View ©2024 Yole SystemPlus

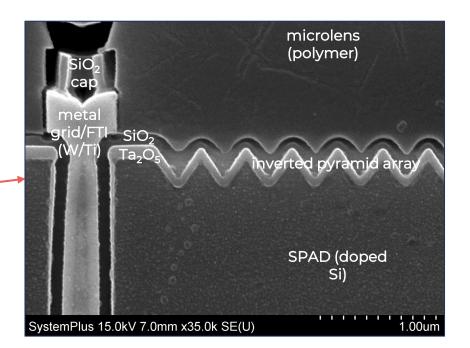


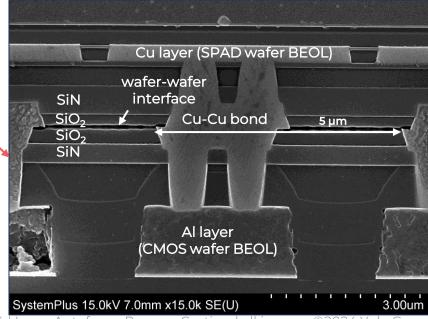
Cross Section through the SPAD
Pixel Array - SEM View ©2024 Yole SystemPlus



CMOS Die Overview w/ Main Blocks @2024 Yole SystemPlus









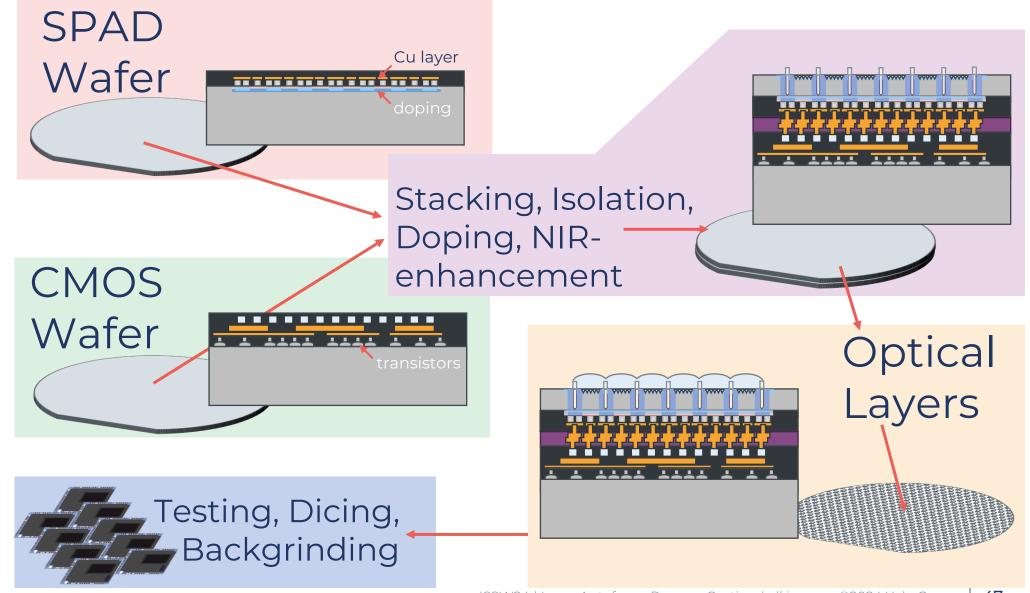
### Outline

- 1. Smartphone 3D Imaging and Laser Autofocus
- 2. 3 systems
  - iPhone 15 Pro LiDAR module by Sony
  - VL53L5 by STMicroelectronics
  - TMF8821 by ams AG
- 3. Reverse Costing Methodology
- 4. Approximative Model
- 5. Results & Discussion

- « Reverse Costing Methodology »
  - 1. Detailed Physical Analysis
  - 2. Reverse Engineer Manufacturing Process
  - 3. Supply Chain & Financial Analysis
  - 4. Simulate Manufacturing Process to Calculate Cost



### Reverse Engineer the Manufacturing Process





### Reverse Engineer the Manufacturing Process

· Oxide + Nitride Deposition Via Lithography Metalization (Cu/Ta/TaN) Prep SPAD Planarization & CMOS Wafers Plasma Activation Bonding Annealing Bonding Thinning · Implantation & Annealing · Isolation Trench Finish Pixels · NIR Enhancement + ARC Grid (Oxide/W/Ti) Pads Guard Ring & Pads

Oxide Deposition (PECVD) Oxide Deposition (PECVD) Via lithography (Lithography 1) Via lithography (Lithography 1) Dry Etching Nitride Dry Etching Nitride Photoresist Ashina Photoresist Ashina Metal Lithography (Lithography 2) Metal Lithography (Lithography 2) Dry Etching Oxide Dry Etching Oxide Photoresist Ashina Photoresist Ashina ALD - TaN Barrier deposit ALD - TaN Barrier deposit PVD - Ta Barrier deposit PVD - Ta Barrier deposit PVD-Copper (Cu) PVD-Copper (Cu) Electroplating-Copper Cu Electroplating-Copper Cu RTA - annealing Cu RTA - annealing Cu CMP Planarisation Metallization CMP Planarisation Metallization Plasma activation Plasma activation Bonding - Molecular Oxide Bonding Bonding - Annealing Thinning - Grinding Thinning - Wet Etching

Thinning - CMP
Dopant gradient - Implantation
Dopant gradient - Lithography 5
Dopant gradient - Implantation
Dopant gradient - Resist Strip
Dopant gradient - Laser Annealing
Trench - Lithography 6
Trench - Dry Etching Silicon
Trench - Resist Strip
Trench - ALD - Aluminum Oxide
NIR Enhancement - Lithography 7
NIR Enhancement - KOH Etch
NIR Enhancement - Resist Strip
Trench/Surface - PVD - Tantalum Oxide
Trench/Surface - HDP Oxide

Tungsten grid - Lithography 8 Tungsten grid - Oxide Etching (Dry) Tungsten grid - Resist Strip Tungsten grid - Ti Deposition Tungsten grid - W Deposition Tungsten grid - Lithography 9 Tungsten grid - W Etching Tungsten grid - Resist Strip Oxide Cap - Lithography 10 Oxide Cap - HDP Oxide Oxide Cap - Resist Strip Pad Trench - Lithography 11 Pad Trench - Silicon Etching (Dry) Pad Trench - Resist Strip Pad Trench - Lithography 12 Pad Trench - Silicon Etching (Dry) Pad Trench - IMD Etching

Pad Trench - Resist Strip



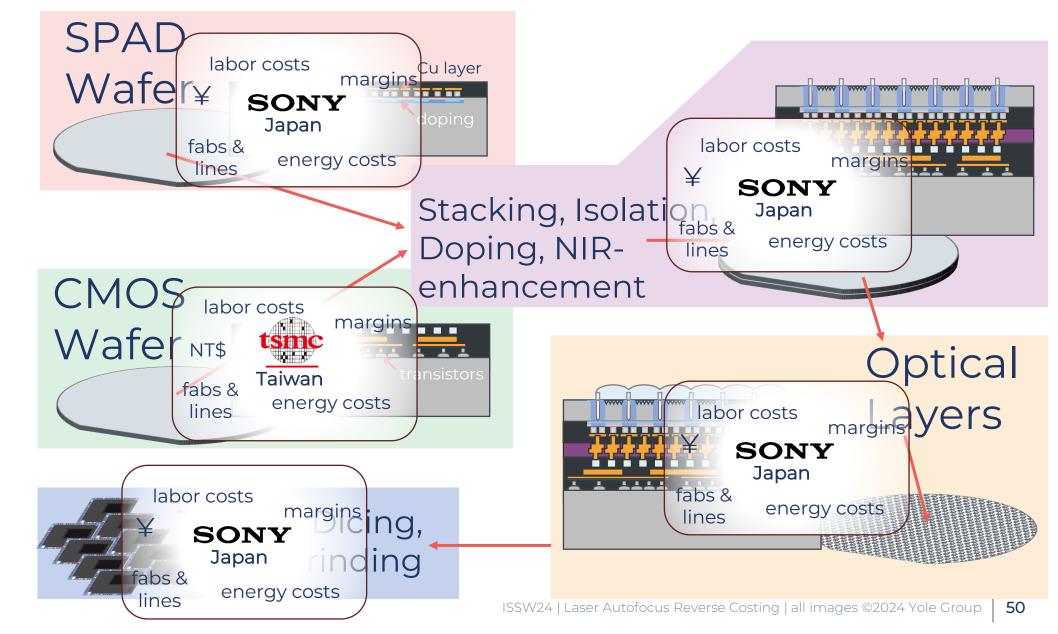
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# Supply Chain and Financial Analysis





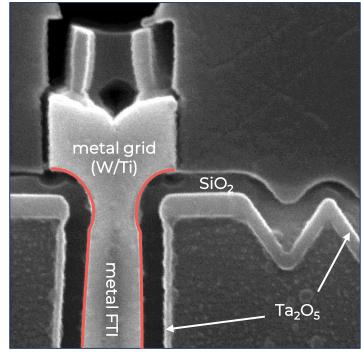
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# **Cost Modeling Overview**



Cross Section through of Inverted Pyramid Array and Metal Grid - SEM View ©2024 Yole SystemPlus



- · Grid (Oxide/W/Ti)
- Pads

Operation name	Step Cost
Operation name	(USD/Wafer)
Tungsten grid - Lithography 8	\$18.05
Tungsten grid - Oxide Etching (Dry)	\$0.95
Tunasten arid - Resist Strip	\$2.26
Tungsten grid - Ti Deposition	\$2.95
Tungsten grid - W Deposition	\$5.11
Tungsten grid - Lithography 9	\$18.05
Tungsten grid - W Etching	\$1.08
Tungsten grid - Resist Strip	\$2.26
Oxide Cap - Lithography 10	\$18.05
Oxide Cap - HDP Oxide	\$14.33
Oxide Cap - Resist Strip	\$2.26
Pad Trench - Lithography 11	\$18.05
Pad Trench - Silicon Etching (Dry)	\$2.04
Pad Trench - Resist Strip	\$2.26
Pad Trench - Lithography 12	\$18.05
Pad Trench - Silicon Etching (Dry)	\$1.32
Pad Trench - IMD Etching	\$3.66
Pad Trench - Resist Strip	\$2.26



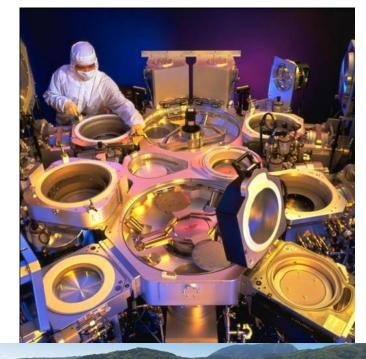
### **Cost Modeling Overview**

Tungsten grid - Ti Deposition

\$2.95

### Operation (PVD of Ti)

- Wafer spends a certain amount of time in the PVD sputtering equipment.
- The equipment occupies costly cleanroom space.
- The machine is managed by an operator.
- The process consumes a certain amount of Ti target.



# Cost Components to calculate:

- Equipment depreciation
- Equipment maintenance
- Cleanroom depreciation
- Cleanroom maintenance
- Labor cost
- Consumable cost
- Energy cost



Overhead

\$2.95



### **Cost Modeling Overview**

# Cost Model Parameters (non-exhaustive)

- Equipment details
  - Purchase cost & date
  - Depreciation scheme
  - Maintenance costs
  - · Footprint & power
  - · Operator time
  - Batch size & loading time
  - Uptime
- Cleanroom details
  - ISO class & constr. date
  - Depreciation scheme
  - Maintenance costs
  - Total area, % load
  - · Hours per year
- Country details
  - Salary
  - Energy cost
  - Shift and supervisor structure
  - Govt. incentives
- Consumables costs
- Process
  - Growth rate
  - Consumable consumption
  - Throughput



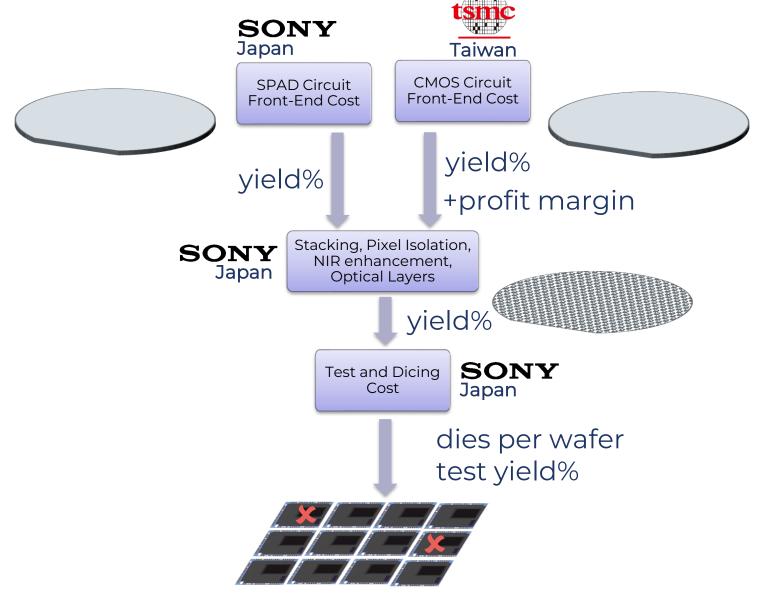


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Pad Trench - Resist Strip	\$2.26



### Die Cost Model Overview





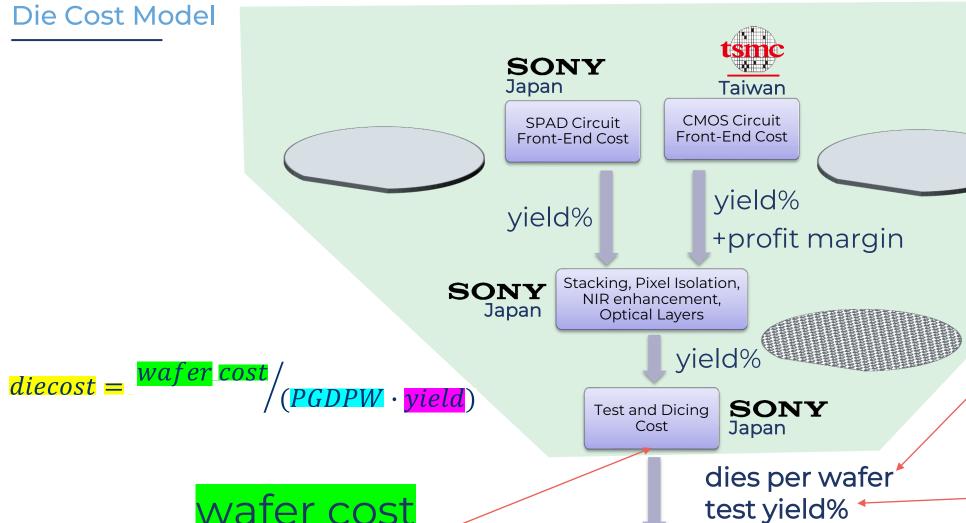
### LASER AUTOFOCUS REVERSE COSTING

### **Presentation Outline**

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### APPROXIMATIVE COSTING MODEL



# wafer cost

rounded to nearest most significant figure



rounded to nearest most significant figure

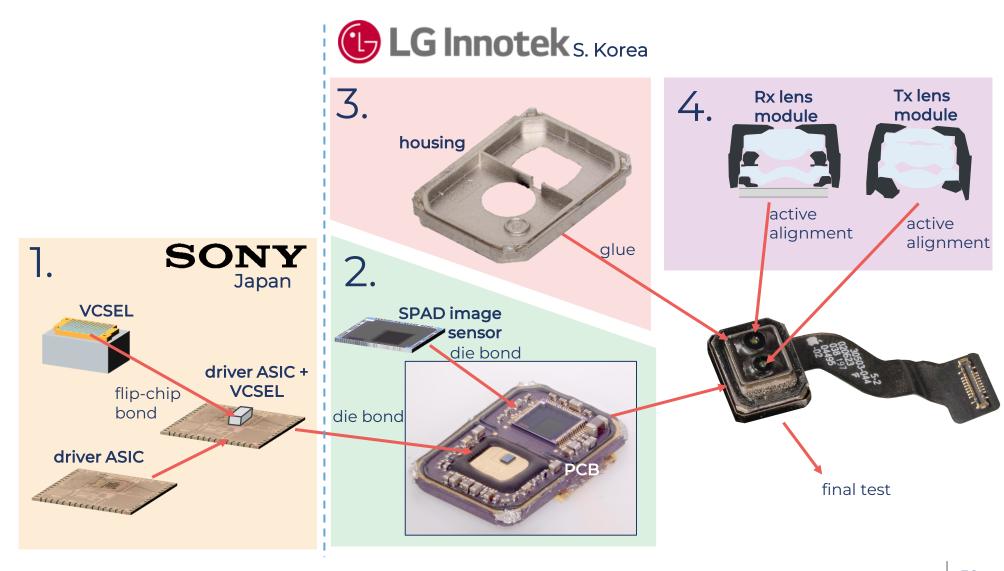


rounded to nearest most significant figure



### APPROXIMATIVE COSTING MODEL

### Module Cost Model



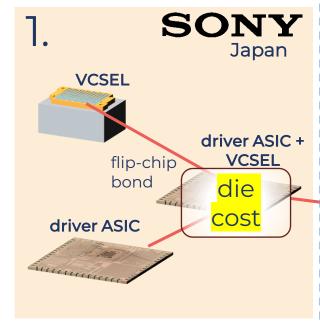


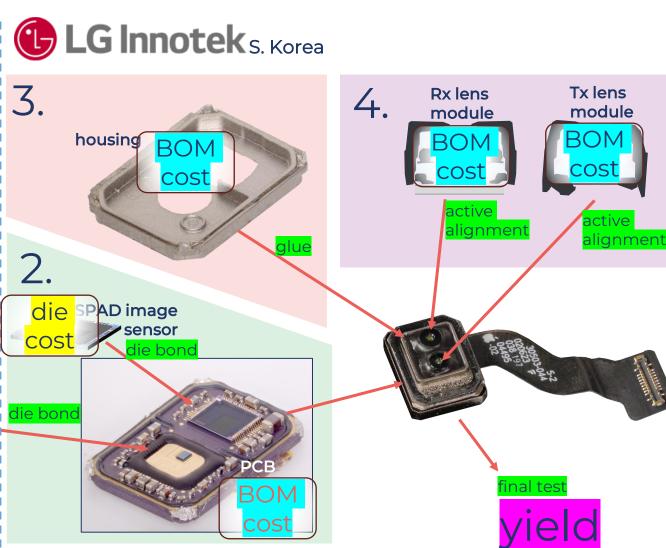
### APPROXIMATIVE COSTING MODEL

### **Module Cost Model**



All components rounded to nearest most significant figure







### LASER AUTOFOCUS REVERSE COSTING

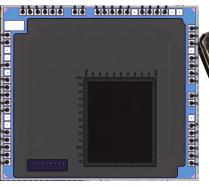
### **Presentation Outline**

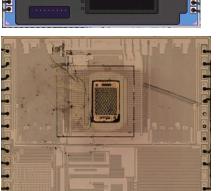
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### **Die Costs**









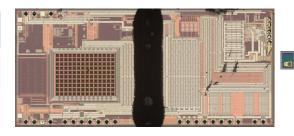
### SONY

Die	wafercost	PGDPW	yield	diecost
SPAD CIS	\$5,000	9,000	80%	\$0.69
VCSEL+Driver	\$6,000	7,000	70%	\$1.22

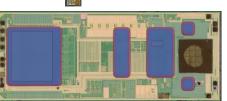




Die	wafercost	PGDPW	yield	diecost
SPAD ASIC	\$2,000	10,000	90%	\$0.22
VCSEL	\$2,000	200,000	90%	\$0.01







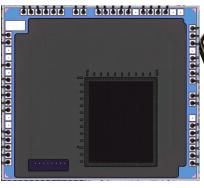


Die	wafercost	PGDPW	yield	diecost
SPAD ASIC	\$3,000	10,000	90%	\$0.33
VCSEL	\$3,000	200,000	90%	\$0.02



### **Die Costs**



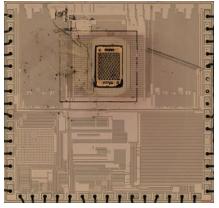




### SONY

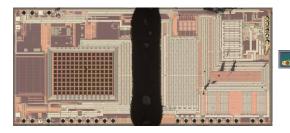
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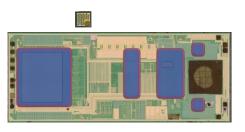
3D-integrated SPAD is costly





Die	wafercost	PGDPW	yield	diecost
SPAD ASIC	\$2,000	10,000	90%	\$0.22
VCSEL	\$2,000	200,000	90%	\$0.01





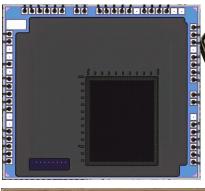


Die	wafercost	PGDPW	yield	diecost
SPAD ASIC	<b>\$3,000</b>	10,000	90%	\$0.33
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### **Module Costs**

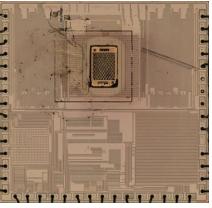






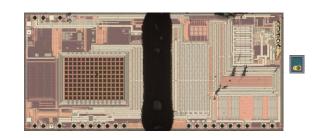
### SONY

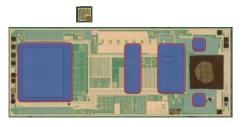
$\sum diecosts$	∑BOMcosts	assembly	Yield	cost
\$1.91	\$3	\$1	90%	\$6.60





∑diecosts	∑BOMcosts	assembly	Yield	cost
\$0.23	\$0.1	\$0.2	90%	\$0.60





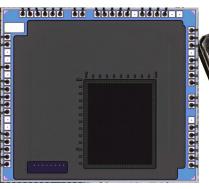


∑diecosts	∑BOMcosts	assembly	Yield	cost
\$0.35	\$0.02	\$0.1	90%	\$0.50



### **Module Costs**





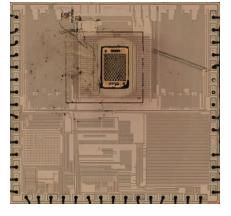


### SONY

∑diecosts	∑BOMcosts	assembly	Yield	cost
\$1.91	<b>\$3</b>	<mark>\$1</mark>	90%	\$6.60

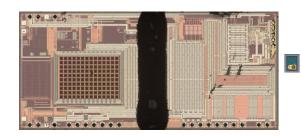
Optics and active alignment in the LiDAR are costly.

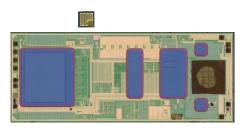
STMicro module also has active alignment of Rx optic.





∑diecosts	∑BOMcosts	assembly	Yield	cost
\$0.23	<mark>\$0.1</mark>	<b>\$0.2</b>	90%	\$0.60







∑diecosts	∑BOMcosts	assembly	Yield	cost
\$0.35	\$0.02	<b>\$0.1</b>	90%	\$0.50



# **Key Findings**

	SONY		amu	
TABLE 1. KEY FINDINGS OF PHYSICAL & COSTING ANALYSIS				
	iPhone LiDAR	VL53L5	TMF8821	
estimated cost	\$6.60	\$0.60	\$0.50	
SPAD ASIC Cost	-	\$0.22	\$0.33	
VCSEL (alone)	-	\$0.01	\$0.02	
Total Die Cost	\$1.91	\$0.23	\$0.35	
Total BOM costs	\$3	\$0.1	\$0.02	
Assembly costs	\$1	\$0.2	\$0.1	
module vol. (LxWxH=V)	$10.3x7.6x3.0 = 235 \text{ mm}^3$	$6.4x3.0x1.5 = 29 \text{ mm}^3$	$4.6x2.0x1.4 = 13 \text{ mm}^3$	
VCSEL cavities	112 (indep.)	5	33	
VCSEL total cavity area <sup>a</sup>	12,650 µm²	1,150 µm²	5,400 μm²	
transmission optic	refractive lens module	diffractive optic	multi-lens diffusor	
emission shape	8x14 dot pattern	square	diffuse	
baseline	3.0 mm	4.0 mm	2.4 mm	
reception optics	refractive lenses, bandpass filter plate, on- chip µlenses, NIR enhanced	Fresnel-like flat lens, on-chip µlenses	WLO refractive lens, on-chip interferometric layers	
SPAD process	90nm on 28nm CMOS with in-pixel DBI [1]	40nm CMOS [3-5]	55nm high-voltage CMOS & DMOS [6]	
pixel pitch	10.1x10.1 µm²	54x54 μm <sup>2,b</sup>	38.8x16.8 µm <sup>2</sup>	
detecting area per pixel	68 µm² (µlens area)	1100 µm² (µlens area)b	132 µm²	
SPAD array resolution	10,672 (116 x 92)	140 (14 x 10) <sup>b</sup>	612 (34 x 18)	
total detecting area	0.73 mm <sup>2</sup>	0.15 mm <sup>2</sup>	0.08 mm <sup>2</sup>	

a Cavity estimated by aperture in the anode

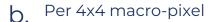




# Key Findings – LiDAR vs multi-zone ranging

	SONY			
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SPAD process	90nm on 28nm CMOS with in-pixel DBI [1]	40nm CMOS [3-5]	55nm high-voltage CMOS & DMOS [6]	
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a. Cavity estimated by aperture in the anode





### Key Findings – LiDAR vs multi-zone ranging

#### SONY TABLE 1. KEY FINDINGS OF PHYSICAL & COSTING ANALYSIS iPhone LiDAR VL53L5 estimated cost \$6.60 \$0.60 SPAD ASIC Cost \$0.22 \$0.01 VCSEL (alone) \$1.91 \$0.23 **Total Die Cost** \$0.1 **Total BOM costs** lens modules \$0.2 Assembly costs module vol. $10.3x7.6x3.0 = 235 \text{ mm}^3$ $6.4 \times 3.0 \times 1.5 = 29 \text{ mm}^3$ (LxWxH=V)**VCSEL** cavities 112 (indep.) VCSEL total cavity $\times 10$ 12,650 µm<sup>2</sup> 1,150 µm<sup>2</sup> areaa transmission refractive lens module diffractive optic optic emission shape 8x14 dot pattern square baseline 3.0 mm 4.0 mm refractive lenses, bandpass filter plate, on-Fresnel-like flat lens. reception optics chip µlenses, NIR enhanced on-chip µlenses SPAD process 90nm on 28nm CMOS with in-pixel DBI [1] 40nm CMOS [3-5] 10.1x10.1 µm<sup>2</sup> 54x54 µm<sup>2,b</sup> pixel pitch 68 µm<sup>2</sup> detecting area 1100 µm<sup>2</sup> (µlens area)<sup>b</sup> per pixel (µlens area) 140 SPAD array 10.672 resolution $(116 \times 92)$ $(14 \times 10)^{b}$ total detecting

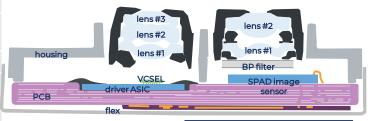
a. Cavity estimated by aperture in the anode

 $0.73 \, \text{mm}^2$ 

b Per 4x4 macro-pixel

### LiDAR 10x more costly

- Large SPAD CIS with costly 3D-integration
- Large back-emitting VCSEL flip-chip bonded directly to driver
- Complex optics for both Rx and Tx







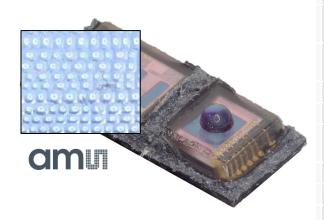
area

 $0.15 \, \text{mm}^2$ 

## VL53L5 vs TMF8821 – WLO vs optical dies

estimated cost		
SPAD ASIC Cost		
VCSEL (alone)		
Total Die Cost		
Total BOM costs		
Assembly costs		
module vol.		
(LxWxH=V)		
VCSEL cavities		
VCSEL total cavity		
area <sup>a</sup>		
transmission		
optic		
emission shape		
baseline		
reception optics		
SPAD process		
pixel pitch		
detecting area		
per pixel		
SPAD array		
resolution		
total detecting		
area		

- WLO Rx inexpensive compared to sophisticated diffractive element
  - Downside: no µlens
- No active alignment in ams AG module





DINGS OF PHYSICAL & COSTING A	NALYSIS	
VL53L5		TMF8821
<mark>\$0.60</mark>		<mark>\$0.50</mark>
\$0.22		\$0.33
\$0.01	000 HI	<b>EPTAGON</b> ™ \$0.02 \$0.35
diffractive \$0.23		Ţ 0.00
<b>~~</b>	WLO i	nexpensive \$0.02
optical dies <sup>\$0.2</sup>		·
$6.4x3.0x1.5 = 29 \text{ mm}^3$		$4.6x2.0x1.4 = 13 \text{ mm}^3$
5		33
1,150 µm²		5,400 μm²
diffractive optic		multi-lens diffusor
square		diffuse
4.0 mm		2.4 mm
Fresnel-like flat lens, <b>on-chip µlenses</b>		WLO refractive lens, on-chip interferometric layers
40nm CMOS [3-5]		55nm high-voltage CMOS & DMOS [6]
54x54 µm <sup>2,b</sup>		38.8x16.8 µm <sup>2</sup>
1100 µm² (µlens area)b		132 µm²
140 (14 × 10) <sup>b</sup>		612 (34 x 18)
µlenses 0.15 mm² n		o µlenses 0.08 mm²



### VL53L5 vs TMF8821 – TSMC

estimated cost		
SPAD ASIC Cost		
VCSEL (alone)		
Total Die Cost		
Total BOM costs		
Assembly costs		
module vol.		
(LxWxH=V)		
VCSEL cavities		
VCSEL total cavity		
area <sup>a</sup>		
transmission		
optic		
emission shape		
baseline		
reception optics		
SPAD process		
pixel pitch		
detecting area		
per pixel		
SPAD array		
resolution		
to <b>tal detecting</b>		
area		

ams AG must compensate for smaller detecting area

Foundry partner makes
SPAD ASIC costly for ams
AG

Ay/	dmi
DINGS OF PHYSICAL & COSTING ANALYSIS	
VL53L5	TMF8821
\$0.60	\$0.50 TC \ 1 C \ 2000
\$0.22	TSMC\$0.33
\$0.01 \$0.23	\$0.02 \$0.35
\$0.23	\$0.02
\$0.2	\$0.1
6.4x3.0x1.5 = 29 mm <sup>3</sup>	4.6x2.0x1.4 = 13 mm <sup>3</sup>
5	33
1,150 µm²	5,400 μm²
diffractive optic	multi-lens diffusor
square	diffuse
4.0 mm	2.4 mm
Fresnel-like flat lens, on-chip µlenses	WLO refractive lens, on-chip interferometric layers
40nm CMOS [3-5]	55nm high-voltage CMOS & DMOS [6]
54x54 μm <sup>2,b</sup>	38.8x16.8 µm²
1100 µm² (µlens area)b	132 μm²
140 (14 x 10) <sup>b</sup>	/2 612 (34 × 18)
0.15 mm <sup>2</sup>	small 0.08 mm²
d	etecting area

a Cavity estimated by aperture in the anode

b Per 4x4 macro-pixel



### VL53L5 vs TMF8821 – VCSEL solution

estimated cost
SPAD ASIC Cost
VCSEL (alone)
Total Die Cost
Total BOM costs
Assembly costs
module vol.
(LxWxH=V)
VCSEL cavities
VCSEL total cavity
areaª
transmission
optic
emission shape
baseline
reception optics
SPAD process
pixel pitch
detecting area
per pixel
SPAD array
resolution
total detecting
area
_

ams AG must compensate for smaller detecting area

- Foundry partner makes SPAD ASIC costly for ams AG
- Powerful VCSEL
  - downside: power hungry

Ay/	amu	
DINGS OF PHYSICAL & COSTING ANALYSIS		
VL53L5	TMF8821	
\$0.60	\$0.50	
\$0.22	\$0.33	
\$0.01	\$0.02	
\$0.23 \$0.1	\$0.35 \$0.02	
\$0.1	\$0.02	
·		
6.4x3.0x1.5 = 29 mm <sup>3</sup>	4.6x2.0x1.4 = 13 mm <sup>3</sup>	
5	$\times 5$ 33	
1,150 µm² powe	rful VCSEL5,400 µm²	
diffractive optic	multi-lens diffusor	
square	diffuse	
4.0 mm	2.4 mm	
Fresnel-like flat lens, on-chip µlenses	WLO refractive lens, on-chip interferometric layers	
40nm CMOS [3-5]	55nm high-voltage CMOS & DMOS [6]	
54x54 µm <sup>2,b</sup>	38.8x16.8 µm <sup>2</sup>	
1100 µm² (µlens area)b	132 μm²	
140 (14 x 10) <sup>b</sup>	/2 612 (34 x 18)	
0.15 mm <sup>2</sup>	small 0.08 mm²	
C	detecting area	

a Cavity estimated by aperture in the anode

h Per 4x4 macro-pixel



### LASER AUTOFOCUS REVERSE COSTING

### Conclusions

#### 3D Imaging (LiDAR) is 10x the cost and 10x the module volume

- Large SPAD CIS with costly 3D-integration
- Large and innovative back-emitting VCSEL flip-chip bonded directly to driver
- Complex optics for both Rx and Tx

STMicroelectronics module has highly engineered optics, including microlenses

#### ams AG module designed to optimize costs

- Heptagon WLO very inexpensive
  - Downside: doesn't allow µlenses
  - Downside: Tx pattern less engineered
- Challenge: Small sensitive area (no µlens, TSMC partner)
  - Solution: compensate with large VCSEL (power hungry)

Fin.

